Octal Bus Buffer

The MC74VHCT541A is an advanced high speed CMOS octal bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHCT541A is a noninverting, 3–state, buffer/line driver/line receiver. When either $\overline{OE1}$ or $\overline{OE2}$ is high, the terminal outputs are in the high impedance state.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The VHCT541A input and output (when disabled) structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. These input and output structures help prevent device destruction caused by supply voltage—input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- High Speed: $t_{PD} = 5.4 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A \text{ (Max)}$ at $T_A = 25 \text{°C}$
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 4.5 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 1.6 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

- Chip Complexity: 134 FETs or 33.5 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

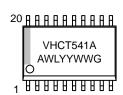


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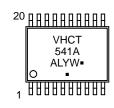
http://onsemi.com

MARKING DIAGRAMS













A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or = Pb-Free Package

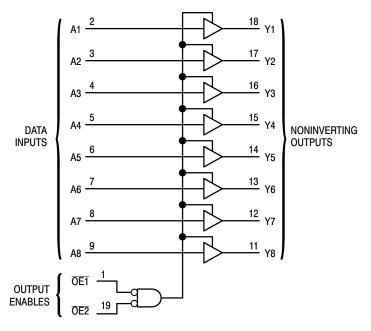
(Note: Microdot may be in either location)

FUNCTION TABLE

	Inputs	Output V			
OE1	OE2	Α	Output Y		
᠘.	. اــ	: ∟	∟:		
L H	l L l X	H X	H Z		
X	Н	X	Z		

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.



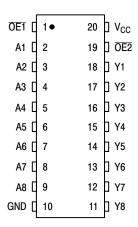


Figure 2. Pin Assignment

Figure 1. Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		- 0.5 to + 7.0	V
V _{in}	DC Input Voltage		- 0.5 to + 7.0	V
V _{out}		tputs in 3–State gh or Low State	- 0.5 to + 7.0 - 0.5 to V _{CC} + 0.5	V
I _{IK}	Input Diode Current		- 20	mA
I _{OK}	Output Diode Current (V _{OUT} < GND	$V; V_{OUT} > V_{CC}$	± 20	mA
l _{out}	DC Output Current, per Pin		± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND	Pins	± 75	mA
P _D		SOIC Package† SOP Package†	500 450	mW
T _{stg}	Storage Temperature		- 65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating – SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V _{CC}	DC Supply Voltage		4.5	5.5	V
V _{in}	DC Input Voltage		0	5.5	V
V _{out}		uts in 3–State n or Low State	0	5.5 V _{CC}	V
T _A	Operating Temperature		- 40	+ 85	°C
t _r , t _f	Input Rise and Fall Time V _{CC}	=5.0V ±0.5V	0	20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	T _A = 25°C		°C	$T_A = -40$	0 to 85°C	
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		4.5 to 5.5	2.0			2.0		V
V _{IL}	Maximum Low-Level Input Voltage		4.5 to 5.5			0.8		0.8	V
V _{OH}	Minimum High–Level Output	$I_{OH} = -50\mu A$	4.5	4.4	4.5		4.4		V
	Voltage $V_{in} = V_{IH}$ or V_{IL}	I _{OH} = - 8mA	4.5	3.94			3.80		•
V _{OL}	Maximum Low-Level Output	I _{OL} = 50μA	4.5		0.0	0.1		0.1	V
	Voltage $V_{in} = V_{IH}$ or V_{IL}	I _{OL} = 8mA	4.5			0.36		0.44	•
I _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0	μΑ
I _{OZ}	Maximum 3–State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	5.5			± 0.25		± 2.5	μА
I _{CC}	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			4.0		40.0	μΑ
Ісст	Quiescent Supply Current	Per Input: V _{IN} = 3.4V Other Input: V _{CC} or GND	5.5			1.35		1.50	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5V	0			0.5		5.0	μА

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0 \text{ns}$)

			T _A = 25°C		°C	$T_A = -40$) to 85°C		
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to Y	$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15pF$ $C_L = 50pF$		5.0 5.5	6.9 7.9	1.0 1.0	8.0 9.0	ns
t _{PZL} , t _{PZH}	Output Enable Time, OE to Y	$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$	$C_L = 15pF$ $C_L = 50pF$		8.3 8.8	11.3 12.3	1.0 1.0	13.0 14.0	ns
t _{PLZ} , t _{PHZ}	Output Disable Time, OE to Y	$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$	C _L = 50pF		9.4	11.9	1.0	13.5	ns
t _{OSLH} , t _{OSHL}	Output to Output Skew	V _{CC} = 5.0 ± 0.5V (Note 1)	C _L = 50pF			1.0		1.0	ns
C _{in}	Maximum Input Capacitance				4	10		10	pF
C _{out}	Maximum 3–State Output Capacitance (Output in High Impedance State)				9				pF

		Typical @ 25°C, V _{CC} = 5.0V	
C_PD	Power Dissipation Capacitance (Note 2)	19	pF

NOISE CHARACTERISTICS (Input $t_f = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

		T _A = 25°C		
Symbol	Parameter	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	1.2	1.6	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-1.2	-1.6	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/8$ (per bit). C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHCT541ADWG	SOIC-20WB (Pb-Free)	38 Units / Rail
MC74VHCT541ADWRG	SOIC-20WB (Pb-Free)	1000 / Tape & Reel
MC74VHCT541ADTG	TSSOP-20 (Pb-Free)	75 Units / Rail
MC74VHCT541ADTRG	TSSOP-20 (Pb-Free)	2500 / Tape & Reel
NLV74VHCT541ADTRG*	TSSOP-20 (Pb-Free)	2500 / Tape & Reel
MC74VHCT541AMELG	SOEIAJ-20 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

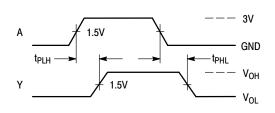


Figure 3. Switching Waveform

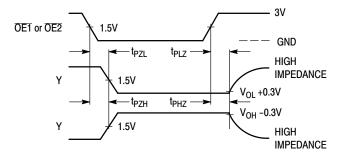
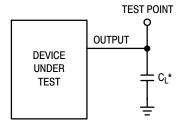
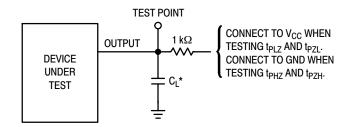


Figure 4. Switching Waveform



*Includes all probe and jig capacitance

Figure 5. Test Circuit



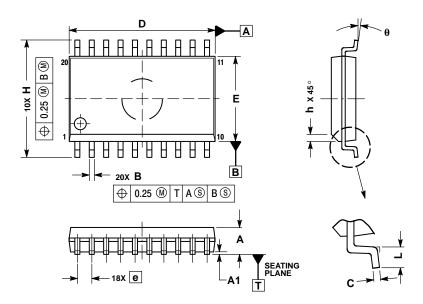
*Includes all probe and jig capacitance

Figure 6. Test Circuit

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

SOIC-20 WB **DW SUFFIX** CASE 751D-05 ISSUE G

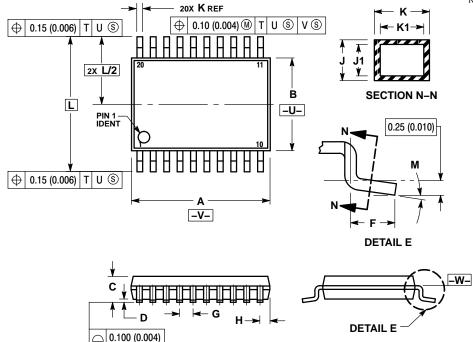


- NOTES:
 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	MILLIMETERS			
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
E	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
θ	0 °	7 °			

PACKAGE DIMENSIONS

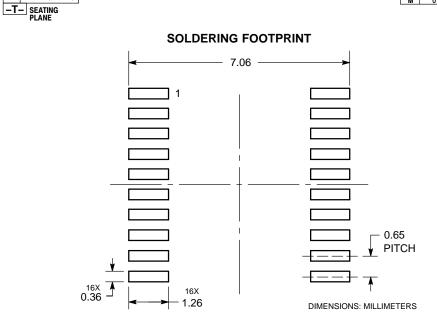
TSSOP-20 CASE 948E-02 **ISSUE C**



NOTES:

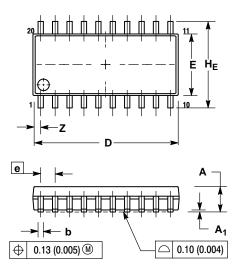
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

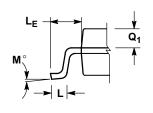
	MILLIN	IETERS	INC	HES		
DIM	MIN	MAX	MIN	MAX		
Α	6.40	6.60	0.252	0.260		
В	4.30	4.50	0.169	0.177		
С		1.20		0.047		
D	0.05	0.15	0.002	0.006		
F	0.50	0.75	0.020	0.030		
G	0.65	BSC	0.026	BSC		
Н	0.27	0.37	0.011	0.015		
J	0.09	0.20	0.004	0.008		
J1	0.09	0.16	0.004	0.006		
K	0.19	0.30	0.007	0.012		
K1	0.19	0.25	0.007	0.010		
L	6.40	BSC	0.252 BSC			
М	0°	8°	0°	8°		



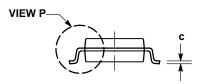
PACKAGE DIMENSIONS

SOEIAJ-20 **M SUFFIX CASE 967 ISSUE A**





DETAIL P



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.
- B. DIMENSIONS D AND E DO NOT INCLUDE
 MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE
 BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	-	2.05		0.081	
A ₁	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
C	0.15	0.25	0.006	0.010	
D	12.35	12.80	0.486	0.504	
Е	5.10	5.45	0.201	0.215	
е	1.27	BSC	0.050	BSC	
HE	7.40	8.20	0.291	0.323	
L	0.50	0.85	0.020	0.033	
LE	1.10	1.50	0.043	0.059	
M	0 °	10°	0 °	10 °	
Q_1	0.70	0.90	0.028	0.035	
Z		0.81		0.032	

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